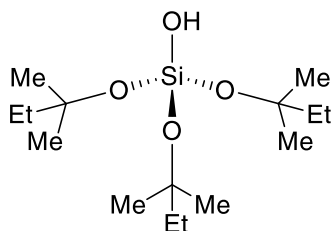


Catalog # 14-7020 Tri-t-pentoxysilanol (99.999%-Si) PURATREM



Thermal Behavior:

- 96-99°C/2.5 Torr
- Vapor pressure: 2 Torr/100°C [1]

Technical Notes:

1. ALD precursor for silicon containing thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
SiO ₂	ALD	75-150°C	~1 Torr	H ₂ O	125-300°C	2-4
Hf _x Si _{1-x} O ₂	ALD	-	-	[Et ₂ N] ₄ Hf	200-370°C	5

References:

1. *US Patent # 7097878 B1 (2006)*..
2. *Chem. Mater.* **2008**, *20*, 7031.
3. *ACS Appl. Mater. Interfaces* **2011**, *3*, 1633.
4. *Mater. Chem. Phys.* **2013**, *142*, 614.
5. *J. Electrochem. Soc.* **2009**, *156*, G89.